Mono N-Type Silicon Wafer(M10)

182.2x182.2

Geometric Parameter

Side length	182.2±0.25mm
Diagonal	247±0.25mm
Thickness	130(+10/-8)μm
Arc length projection	7.72±0.5mm

Electrical Properties

Resistivity	0.6-1.6Ω·cm
Minority carrier	≥1000μs
Oxygen content	≤$5.75\text{x}10^{17}$at/cm^3
Carbon content	≤$5\text{x}10^{16}$at/cm^3

Material Properties

Growth method	CZ
Orientation	<100>±2°

Surface Performance

TTV	≤20
Warpage	≤40
Line mark	≤13
Edge collapse	Depth≤0.3mm, length≤0.5mm, no more than one places
Cracks and perforations	Invisible by visual inspection
Silicon wafer surface	Clean, free of oil, soap, glue and other residues